Semiconductors
High-reliability discrete products and engineering services since 1977

## FJT1100, FJT1101

## ULTRA LOW LEAKAGE DIODES

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

| Characteristics | Value |
| :--- | :--- |
| Storage temperature range | $-65^{\circ}$ to $+200^{\circ} \mathrm{C}$ |
| Maximum junction operating temperature | $+175^{\circ} \mathrm{C}$ |
| Lead temperature | $+260^{\circ} \mathrm{C}$ |
| Power dissipation |  |
| Maximum total power dissipation at $25^{\circ} \mathrm{C}$ ambient | 250 mW |
| Linear power derating factor (from $25^{\circ} \mathrm{C}$ ) | $1.67 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Working inverse voltage |  |
| FJT1100 | 25 V |
| FJT1101 | 15 V |
| Continuous forward current | 150 mA |

ELECTRICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Symbol | Characteristics |  | Min | Max | Units | Test Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| BV | Breakdown voltage | $\begin{aligned} & \text { FJT1100 } \\ & \text { FJT1101 } \end{aligned}$ | $\begin{aligned} & 30 \\ & 20 \end{aligned}$ |  | V | $\mathrm{I}_{\mathrm{R}}=5.0 \mu \mathrm{~A}$ |
| $\mathrm{I}_{\mathrm{R}}$ | Reverse current | $\begin{aligned} & \text { FJT1100 } \\ & \text { FJT1101 } \end{aligned}$ |  | $\begin{gathered} 1.0 \\ 10 \\ 5.0 \\ 15 \end{gathered}$ | pA | $\begin{aligned} & V_{R}=5.0 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{R}}=15 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{R}}=5.0 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{R}}=15 \mathrm{~V} \end{aligned}$ |
| $V_{F}$ | Forward voltage | FJT1100 <br> FJT1101 |  | $\begin{aligned} & 1.05 \\ & 1.10 \end{aligned}$ | V | $\mathrm{IF}_{\mathrm{F}}=50 \mathrm{~mA}$ |
| C | Capacitance | $\begin{aligned} & \text { FJT1100 } \\ & \text { FJT1101 } \end{aligned}$ |  | $\begin{aligned} & 1.5 \\ & 1.8 \end{aligned}$ | pF | $V_{R}=0, f=1 \mathrm{MHz}$ |

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MECHANICAL CHARACTERISTICS

| Case | DO-35 |
| :--- | :--- |
| Marking | Body painted, alpha-numeric |
| Polarity | Cathode band |



|  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  | D0-35 |  |  |  |
|  | Inches |  | Millimeters |  |
|  | Min | Max | Min | Max |
| BD | 0.055 | 0.090 | 1.400 | 2.290 |
| BL | 0.120 | 0.200 | 3.050 | 5.080 |
| LD | 0.018 | 0.022 | 0.460 | 0.560 |
| LL | 1.000 | 1.500 | 25.400 | 38.100 |

